

UPG5N120

Insulated Gate Bipolar Transistor

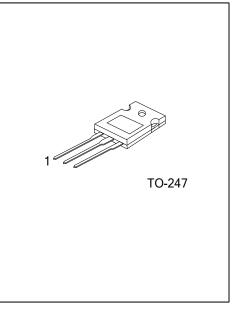
1200V NPT PLANAR IGBT

DESCRIPTION

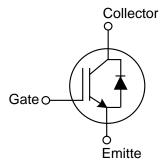
The UTC **UPG5N120** is a 1200V NPT Planar Insulated Gate Bipolar Transistor. it uses UTC's advanced technology to offers superior conduction and switching performance, high avalanche ruggedness and easy parallel operation.

FEATURES

- * High speed switching
- * High input impedance
- * Low saturation voltage: V_{CE(SAT)} =2.25V @ I_C=5.0A



SYMBOL



ORDERING INFORMATION

Ordering Number		Daakaga	Pin Assignment			Dealing	
Lead Free	Halogen Free	Package	1	2	3	Packing	
UPG5N120L-T47-T	UPG5N120G-T47-T	TO-247	С	E	Tube		
Note: Pin Assignment: G: Gate C: Collector E: Emitter							
UPG5N120 <u>G-T47-T</u>	 (1) T: Tube (2) T47: TO-247 (3) G: Halogen Free and Lead Free, L: Lead Free 						



ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT	
Collector-Emitter Voltage		V _{CES}	1200	V	
Gate-Emitter Voltage		V _{GES}	±20	V	
Continuous Collector Current	T _C =25°C		10	А	
	T _C =100°C	I _C	5	А	
Collector Current Pulsed (Note 1)		I _{CM}	20	А	
Power Dissipation		PD	250	W	
Operating Junction Temperature		T_J	-55 ~ +150	°C	
Storage Temperature Range		T _{STG}	-55 ~ +150	°C	

 Notes: 1. Absolute maximum ratings are stress ratings only and functional device operation is not implied. Absolute maximum ratings are those values beyond which the device could be permanently damaged.
 2. Pulse width limited by maximum junction temperature.

THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Case	θ _{JC}	0.42	°C/W	

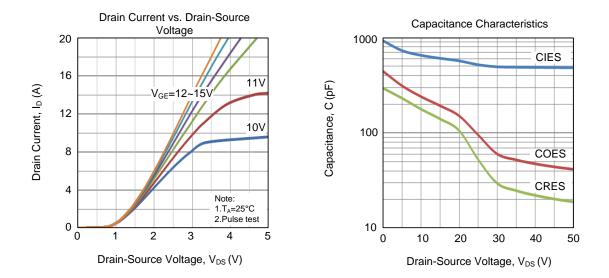
■ ELECTRICAL CHARACTERISTICS (T_c=25°C, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT		
Off Characteristics								
Collector-Emitter Breakdown Voltage	B _{VCES}	I _C =250μA, V _{GE} =0V	1200			V		
Collector Cut-Off Current	I _{CES}	V _{CE} =V _{CES} , V _{GE} =0V			250	μA		
G-E Leakage Current	I _{GES}	$V_{GE}=V_{GES}, V_{CE}=0V$			±250	nA		
On Characteristics								
Gate to Emitter Threshold Voltage	V _{GE(TH)}	I _C =90μA, V _{CE} =V _{GE}	4.0		6.0	V		
Collector to Emitter Saturation Voltage	V _{CE(SAT)}	I _C =5.0A, V _{GE} =15V			2.25	V		
Dynamic Characteristics				-		-		
Input Capacitance	CIES			515		рF		
Output Capacitance	C _{OES}	V _{CE} =25V, V _{GE} =0V, f=1MHz		90		рF		
Reverse Transfer Capacitance	C _{RES}			52		рF		
Switching Characteristics								
Total Gate Charge	Q_{G}	V _{CE} =100V, V _{GE} =15V, I _C =5A		45		nC		
Gate-Emitter Charge	Q_GE	Vc==100V. Vc==15V. Ic=5A		12		nC		
Gate-Collector Charge	Q_{GC}	V _{CE} =100V, V _{GE} =15V, I _C =5A		18		nC		
Turn-On Delay Time	t _{D(ON)}			42		ns		
Rise Time	t _R	V _{CC} =50V, V _{GE} =15V, I _C =5A,		120		ns		
Turn-Off Delay Time	t _{D(OFF)}	R _G =10Ω,		100		ns		
Fall Time	t _F			68		ns		
SOURCE- DRAIN DIODE RATINGS AN	D CHARACT	ERISTICS		-		-		
Forward Voltage Drop	V _{FM}	I _F =5A		1.56		V		
Reverse Recovery Time	t _{rr}	I⊧=5A, dI/dt=200A/µS		115		ns		
Reverse Recovery Charge	Q _{rr}	IF=3A, αι/α(-200A/μ3		307		nC		

UNISONIC TECHNOLOGIES CO., LTD

UPG5N120

TYPICAL CHARACTERISTICS



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